

version, except that marked up versions are not being supplied for any canceled claim.

Please cancel claims 1-32
^{46 50}

Please add claims ~~33-37~~ as follows:

Rule 126
⁴⁶
33. (New) A method of forming a bottom-gated thin film transistor comprising the following steps:

forming a transistor gate;

forming a polycrystalline thin film transistor layer over the transistor gate;

forming a fluorine containing layer proximate the polycrystalline thin film transistor layer; and

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transferring fluorine into the polycrystalline thin film transistor layer from the fluorine containing layer.

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34. (New) The method of claim ⁴⁶33 wherein the polycrystalline thin film transistor layer comprises silicon.

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35. (New) The method of claim ⁴⁶33 wherein the forming a fluorine containing layer comprises forming a sacrificial fluorine containing layer over the thin film transistor layer by chemical vapor deposition utilizing WF_6 and SiH_4 precursors.

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36. (New) The method of claim 33 further comprising, after the transferring fluorine, removing the sacrificial layer from over the thin film transistor layer.

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37. (New) A method of forming a bottom-gated thin film transistor comprising the following steps:

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forming a transistor gate;
forming a polycrystalline thin film transistor layer over the transistor gate;
forming a fluorine containing layer over the polycrystalline thin film transistor layer;
providing a buffering layer intermediate the thin film transistor layer and the fluorine containing layer; and
transferring fluorine into the polycrystalline thin film transistor layer from the fluorine containing layer.
